

## RFUP-PIF1: Silicon MESFET Discrete (Preliminary)

### Features:

- Discrete Silicon MESFET for Power Amplifier and Switching Applications
- Output power up to 30dBm
- Developed on SOI CMOS and can be integrated into any process
- 16V on 45 nm SOI CMOS

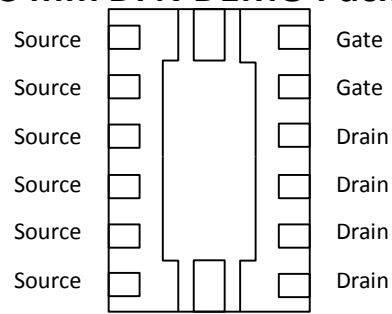
### Applications:

- RF Power Amplifiers
- Low Dropout Regulators
- Switching Converters
- Communication Devices
- Integrate with scaled CMOS (<180nm) for complete digital and high voltage applications

### Description:

RF Micropower has developed a high voltage MESFET which has been demonstrated on multiple conventional SOI CMOS processes. The patented technology allows the fabrication of small form factor, low cost RF Power Transistors targeting up to 5W.

### 2x3 mm DFN DEMO Package:



### Demonstration Power Amplifiers:

